The press service of Tomsk State University (TSU) reported that university scientists developed diodes based on Gaul oxide-promising material for semiconductor devices. The first laboratory samples have already passed tests.

As explained by the graduate student of TSU Nikita Yakovlev, Oxide Gaul belongs to semiconductors of the fourth generation. Such materials are resistant to high stress, efficiency and compact dimensions. Development withstands a voltage of more than 1000 volts.

The project received the support of the Fund for Assistance to Innovations. Now experts are working on optimizing the production process. According to them, new diodes will find use in various areas – from energy -efficient chargers to car control systems.

Although the leader in the development of semiconductors in Gaulic oxide is now China, Russian scientists are actively working in this direction.